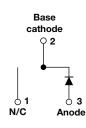
VS-HFA08TB60S-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A





PRIMARY CHARACTERISTICS						
I _{F(AV)}	8 A					
V _R	600 V					
V _F at I _F	1.4 V					
t _{rr} (typ.)	18 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Single					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08TB60S is ideally suited for applications in power supplies (PFC boost diode) and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward current	I _F	T _C = 100 °C	8				
Single pulse forward current	I _{FSM}		60	А			
Maximum repetitive forward current	I _{FRM}		24				
Maximum nature dissinction	P _D	T _C = 25 °C	36	W			
Maximum power dissipation		T _C = 100 °C	14	vv			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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Document Number: 96219

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ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-		
		I _F = 8.0 A	See fig. 1	-	1.4	1.7	V	
Maximum forward voltage	V _{FM}	I _F = 16 A		-	1.7	2.1		
	I _F = 8.0 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 0	-	0.3	5.0		
leakage current	IRM	T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	100	500	μΑ	
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	10	25	pF	
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS (TJ = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/µs, V _R = 30 V	-	18	-		
Reverse recovery time See fig. 5, 6	t _{rr1}	T _J = 25 °C		-	37	55	ns	
000 lig. 0, 0	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	55	90		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	3.5	5.0	Α	
reak lecovery cullent	I _{RRM2}	T _J = 125 °C		-	4.5	8.0		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138	nC	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	124	360		
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	240	-	- A/μs	
	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-	Ανμs	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	3.5	K/W		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	r./ v v		
Weight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Marking device		Case style D ² PAK (TO-263AB)		HFA08	TB60S			



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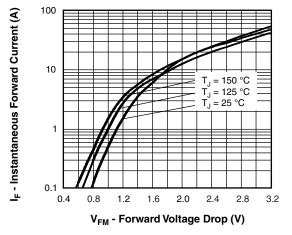


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

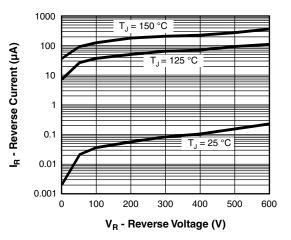


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

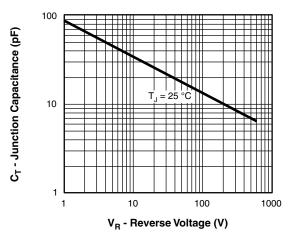


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

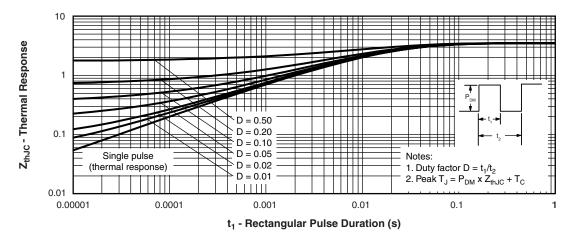


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



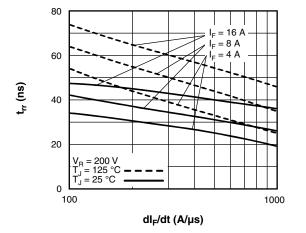


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

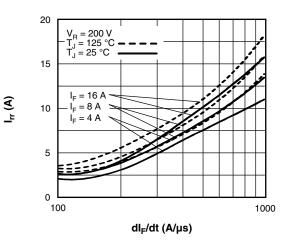


Fig. 6 - Typical Recovery Current vs. dl_F/dt



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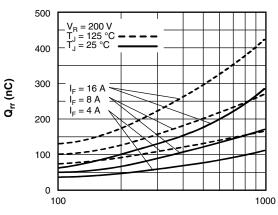




Fig. 7 - Typical Stored Charge vs. dl_F/dt

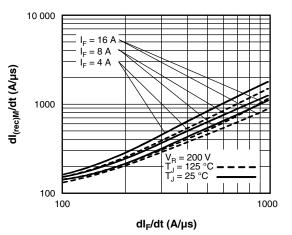


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

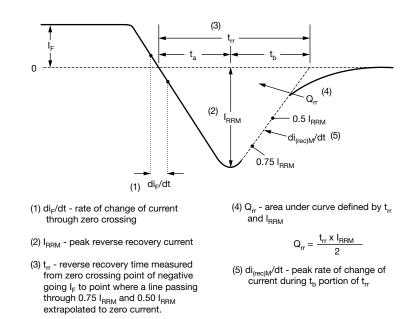


Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	08	тв	60	S	L	-M3
		(2)	(3)	(4)	(5)	(6)		(8)	(9)
	\bigcirc		\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	U	U
	1 ·	· Visl	nay Sem	niconduo	ctors pro	oduct			
	2 ·	· HE	KFRED [®]	family					
	3 ·	· Pro	cess de	signator	: A = ele	ectron ir	radiate	d	
	4 ·	- Cur	rent rati	ng (08 =	= 8 A)				
	5	- Pac	kage ou	utline (T	B = TO-	220, 2 I	eads)		
	6	· Vol	age rati	ng (60 =	= 600 V)				
	7.	• S =	D ² PAK	(TO-26	3AB)				
	8 -	• N	one = tu	be (50 p	pieces)				
		۰L	= tape a	nd reel	(left orie	ented)			
		• R	= tape a	and reel	(right o	riented)	1		
	9 -	- Env	ironmer	ntal digit	:				
		-M3	s = halog	gen-free	, RoHS-	complia	ant, and	termina	ations le

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA08TB60S-M3	50	1000	Antistatic plastic tube					
VS-HFA08TB60SR-M3	800	800	13" diameter reel					
VS-HFA08TB60SL-M3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	MILLIMETERS		INCHES		
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	BSC	0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25 BSC		0.010 BSC			
L4	4.78	5.28	0.188	0.208		

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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